IEEE ANDREW S. GROVE AWARD
RECIPIENTS
(Formerly the IEEE Jack A. Morton Award)

2025 – SAYEEF SALAHUDDIN
Taiwan Semiconductor Manufacturing Company
Distinguished Professor, Electrical Engineering and Computer Sciences, University of California
Berkeley, Berkeley, California, USA
“For pioneering contributions to physics of ferroelectrics and integrated ferroelectric devices.”

2024 – TSUNENOBU KIMOTO
Professor, Kyoto University, Kyoto, Japan
“For contributions to silicon carbide material and power devices.”

2023 – H.-S. PHILIP WONG
Willard R. and Inez Kerr Bell Professor in the School of Engineering, Stanford University, Stanford, California, USA
“For contributions to novel and advanced semiconductor device concepts and their implementation.”

2022 – HEIKI RIEL
IBM Fellow, Lead IBM Research Quantum Europe & Africa, Zurich, Switzerland
“For contributions to materials for nanoscale electronics and organic light-emitting devices.”

2021 – HIDEAKI AOCHI
Senior Expert, Institute of Memory Technology Research and Development, Kioxia Corporation, Kanagawa, Japan
AND
RYOTA KATSUMATA
Deputy General Manager, Advanced Memory Development Center, Kioxia Corporation, Mie, Japan
AND
MASARU KITO
Group Manager, Advanced Memory Development Center, Kioxia Corporation, Mie, Japan
“For pioneering and sustained contributions to high-density, three-dimensional flash memory.”

2020 – EVELYN L. HU
Tarr-Coyne Professor of Applied Physics and Electrical Engineering, John A. Paulson School of Engineering and Applied
“For pioneering contributions to microelectronics fabrication technologies for nanoscale and photonic devices.”
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Sciences, Harvard University, Cambridge, Massachusetts, USA

2019 – DIGH HISAMOTO
Chief Senior Scientist, Hitachi; Ltd., Tokyo, Japan
"For pioneering work in the manufacturing of three-dimensional double-gate MOSFET devices."

2018 – GURTEJ S. SANDHU
Senior Fellow, Director, Emerging Memory Technologies R&D, Micron Technology Inc., Boise, Idaho, USA
"For contributions to silicon CMOS process technology that enable DRAM and NAND memory chip scaling."

2017 – SORIN CRISTOLOVEANU
Director of Research, The French National Centre for Scientific Research, Grenoble, France
"For contributions to silicon-on-insulator technology and thin body devices."

2016 – CARLOS H. DÍAZ
Director, Advanced Logic Technology Development, Taiwan Semiconductor Manufacturing Co., Hsinchu, Taiwan
"For sustained contributions to and leadership in foundry advanced CMOS logic transistor technology."

2015 – MASAYOSHI ESASHI
Professor, Tohoku University, Sendai, Miyagi, Japan
"For developments in micro-electromechanical systems (MEMS) used in transportation and industrial electronics."

2014 – SANJAY BANERJEE
Cockrell Regents Chair Professor of Electrical and Computer Engineering and Director, Microelectronics Center, University of Texas, Austin, Texas, USA
"For contributions to column-IV MOSFETs and related materials processing."

2013 – SHINICHI TAKAGI
Full Professor, The University of Tokyo, Tokyo, Japan
"For contributions to the understanding of transport properties in inversion layers of high-performance MOSFETs."

2012 – JEAN-PIERRE COLINGE
Head of the Micro-Nano Electronics Centre, Tyndall National Institute, University College Cork Cork, Ireland
"For contributions to silicon-on-insulator devices and technology."

2011 – JUDY HOYT
Professor, Massachusetts Institute of Technology, Cambridge, MA, USA
"For seminal contributions to the demonstration of Si/Ge lattice mismatch strain engineering for enhanced carrier transport properties in MOSFET devices."
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AND

EUGENE A. FITZGERALD
Merton C. Flemings SMA Professor of Materials Engineering, Massachusetts Institute of Technology, Cambridge, MA, USA

2010 – BIJAN DAVARI
IBM Fellow, Vice President IBM Corporation Yorktown Heights, NY, USA
“For contributions to high performance deep-submicron CMOS technology.”

2009 – ERIC FOSSUM
Chairman & CEO, Siimpel Corporation, Arcadia, CA, USA
“For significant contributions to the invention, development and commercialization of CMOS image sensors.”

2008 – STEFAN LAI
Retired Vice President, Technology & Manufacturing Group, Intel Corporation, Santa Clara, CA, USA
“For contributions in developing Flash memory into a main stream non-volatile memory and the development of multiple generations of Flash memory technologies”

2007 – JAMES D. PLUMMER
Dean of Engineering Stanford University, Stanford, CA, USA
“For seminal contributions to the modeling, simulation and physics of silicon devices.”

2006 – CHANG-GYU HWANG
President and CEO of Samsung Electronics Co, Ltd Gyeonggi-Do, Korea
“For contributions to the development of advanced memory products.”

2005 – TSO-PING MA
Raymond John Wean Professor and Chairman of Electrical Engineering Yale University, New Haven, CT, USA
“For contributions to the development and understanding of CMOS gate dielectrics.”

2004 – KRISHNA SARASWAT
Professor, Dept of Electrical Engrg Stanford University, Stanford, CA, USA
“For seminal contributions to silicon process technology.”

2003 – MARK BOHR
Fellow, Director of Process "For leadership in scaling of advanced CMOS technology for microprocessors."
IEEE ANDREW S. GROVE AWARD  
RECIPIENTS  
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<table>
<thead>
<tr>
<th>Year</th>
<th>Recipient 1</th>
<th>Recipient 2</th>
<th>Citation</th>
</tr>
</thead>
<tbody>
<tr>
<td>2002</td>
<td>DIMITRI A. ANTONIADIS</td>
<td>Massachusetts Institute of Technology</td>
<td>&quot;For seminal contributions to field-effect devices and silicon process modeling.&quot;</td>
</tr>
<tr>
<td></td>
<td>Intel Corporation, Hillsboro, OR, USA</td>
<td>Cambridge, MA, USA</td>
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<tr>
<td>2001</td>
<td>AL F. TASCH, JR.</td>
<td>University of Texas at Austin, Austin, TX, USA</td>
<td>“For contributions to MOS technology, and ion implantation and device modeling.”</td>
</tr>
</tbody>
</table>

Beginning with the year 2001, the Jack A. Morton Award was renamed the IEEE Andrew S. Grove Award

<table>
<thead>
<tr>
<th>Year</th>
<th>Recipient 1</th>
<th>Recipient 2</th>
<th>Citation</th>
</tr>
</thead>
<tbody>
<tr>
<td>2000</td>
<td>WOLFGANG FICHTNER</td>
<td>Swiss Federal Institute of Technology</td>
<td>“For outstanding contributions to semiconductor device simulations.”</td>
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<tr>
<td></td>
<td>Zurich, Switzerland</td>
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<tr>
<td>1999</td>
<td>CHARLES H. HENRY</td>
<td>Lucent Technologies, Bell Laboratories</td>
<td>&quot;For fundamental contributions to the understanding of the optical properties of quantum wells and semiconductor lasers.&quot;</td>
</tr>
<tr>
<td></td>
<td>Murray Hill, NJ</td>
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</tr>
<tr>
<td>1998</td>
<td>ISAMU AKASAKI</td>
<td>Meijo University</td>
<td>“For contributions in the field of group-III nitride materials and devices.”</td>
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<tr>
<td></td>
<td>Nagoya, Japan</td>
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<tr>
<td></td>
<td>SHUJI NAKAMURA</td>
<td>Nichia Chemical Industries, Ltd.</td>
<td></td>
</tr>
<tr>
<td></td>
<td>Tokushima, Japan</td>
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</tr>
<tr>
<td>1997</td>
<td>CHENMING HU</td>
<td>University of California</td>
<td>&quot;For outstanding contributions to the physics and modeling of MOS device reliability.&quot;</td>
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<tr>
<td></td>
<td>Berkeley, CA, USA</td>
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</tr>
<tr>
<td>1996</td>
<td>ROBERT W. DUTTON</td>
<td>Stanford University</td>
<td>&quot;For seminal contributions to semiconductor process and device modeling.&quot;</td>
</tr>
<tr>
<td></td>
<td>Stanford, CA, USA</td>
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</tr>
<tr>
<td>1995</td>
<td>YOSHIO NISHI</td>
<td>Hewlett-Packard Company</td>
<td>&quot;For contributions to the basic understanding and innovative development of MOS device technology.&quot;</td>
</tr>
<tr>
<td></td>
<td>Palo Alto, CA, USA</td>
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</tr>
</tbody>
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1994 – ROBERT E. KERWIN
AT&T
Warren, NJ, USA
AND
DONALD L. KLEIN
IBM Corporation
Hopewell Junction, NY, USA
AND
JOHN C. SARACE
Rockwell International
Anaheim, CA, USA

"For pioneering work and the basic patent on the self-aligned silicon-gate process, a key element in fabrication of very large scale integrated circuits."

1993 – TOSHIHISA TSUKADA
Hitachi, Ltd.
Tokyo, Japan

"For contributions to the discovery and development of Buried Heterostructure (BH) semiconductor lasers."

1992 – TAKUO SUGANO
University of Tokyo
Tokyo, Japan

"For contributions to Metal-Insulator-Semiconductor Devices and Technology."

1991 – TAK H. NING
HWA N. YU
IBM Corporation
Yorktown Height, NY, USA

"For contributions to the development of advanced bipolar and MOS devices."

1990 – GREGORY E. STILLMAN
University of Illinois
Urbana, IL
and CHARLES M. WOLFE
Washington University
St. Louis, MO, USA

"For the growth and characterization of ultra-high purity gallium arsenide and related compounds."

1989 – CHIH-TANG SAH
University of Illinois
Urbana, IL, USA

"For contributions to the understanding of semiconductor defects and the physics of MOS devices."

1988 – FRANK STERN
IBM Corp.
Yorktown Heights, NY, USA

"For contributions to the theory of injection lasers and two-dimensional electron gases."

1987 – DENNIS D. BUSS
AND
RICHARD A. CHAPMAN
AND
MICHAEL A. KINCH
Texas Instruments
Dallas, TX, USA

"For the demonstration and development of mercury cadmium telluride monolithically- integrated charge-coupled device focal plane arrays."
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1986 – HERBERT KROEMER
University of California
Santa Barbara, CA, USA
"For pioneering the theory and device applications of semiconductor heterostructures."

1985 – ROBERT D. BURNHAM
AND
WILLIAM STREIFER
Xerox Corp.
Palo Alto, CA, USA
AND
DONALD R. SCIFRES
Spectra Diode Laboratories
San Jose, CA, USA
"For contributions to electrically pumped distributed feedback lasers and high-power phased-locked laser arrays."

1984 – HANS S. RUPPRECHT
AND
JERRY M. WOODALL
IBM Corp.
Yorktown Heights, NY, USA
"For pioneering work in gallium aluminum arsenide heterojunctions and high efficiency light emitting diodes and injection lasers prepared by liquid phase epitaxy."

1983 – JUN-ICHI NISHIZAWA
Tohoku University
Sendai, Japan
"For invention and development of the class of static induction transistors (SIT) and for advances in optoelectronic devices."

1982 – DOV FROHMAN-BENTCHKOWSKY
INTEL Elec.
Jerusalem, Israel
"For contributions to non-volatile semiconductor memories."

1981 – NICK HOLONYAK, JR.
University of Illinois
Urbana, IL, USA
"For pioneering work in quantum well lasers and contributions to visible semiconductor lasers and light-emitting diodes."

1980 – JAMES F. GIBBONS
Stanford University
Stanford, CA, USA
"For pioneering contributions to the use of ion implantation in the fabrication of semiconductor devices."

1979 – MARTIN P. LEPSELTHER
Bell Laboratories
Murray Hill, NJ, USA
"For invention of the beam-lead structure and metallurgy used in silicon integrated circuits."

1978 – JURI MATISOO
IBM Corp.
Yorktown Heights, NY, USA
"For pioneering the Josephson computer technology."
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(Formerly the IEEE Jack A. Morton Award)

1977 – MORGAN SPARKS
Sandia Corp.
Albuquerque, NM, USA

"For contributions to solid-state device technology and the management of research and development."

1976 – ROBERT N. HALL
General Electric Co.
Schenectady, NY USA

"For outstanding achievement in solid-state physics and chemistry and the invention and development of semiconductor devices."